Legend – Product name decipher

IGBT Modules

FF	400	R33	K	F	x	example for an IGBT module
FZ						single switch with one IGBT and FWD
FF						half bridge (two IGBTs an FWDs)
FP						Power Integrated Module
FM						Matrix Module
FD/DF						chopper module
FB						Integrated modules in B2 configuration with IGBT & NTC
DD						dual diode module
FR						Switched Reluctance Modul
F3L						3-level configuration
FS3L						3-level 3 phase bridge
FT						tripack
F4						fourpack
F5						fivepack
FS						sixpack
	400					max. DC-collector current (A)
		R				reverse conducting
		S				fast Diode
		33				collector-emitter-voltage in 100 V
			K/H/I/M/N/O/P			mechanical construction:
			W/V/X/Y			module
				F		fast switching type
				H		high speed IGBT
				J		SiC JFET
				L		type with low V_{CEsat}
				M		MOSFET Chip
				S		fast short tail IGBT Chip
				E		low sat and fast trench IGBT
				T		fast trench IGBT
				P		soft switching trench IGBT
					1 ... n	internal reference numbers
					C	Emitter Controlled
					D	higher Diode current
					F	very fast Diode
					G	module in big housing
					I	integrated cooling
					P	with pre applied TIM
					R	reduced number of pins
					T	low temperature type
					-K	design with common cathode
					B1 ... n	Construction variation
					S1 ... n	Electrical selection

MIPAQ

IFF	150	B	12	N3	T	4		
I								MIPAQ™ family
FF								dual switch
FZ								single switch
FT								tripack
FS								3 phase full bridge
FP								power integrated module
	150							max. DC-collector current in A
								integration level:
		B						with current sensors
		S						with full digital current measurement
		V						with gate driver and temperature measurement
			12					collector-emitter-voltage in 100V
								mechanical construction: module
				N1..3				EconoPACK™ 1..3
				P				EconoPACK™ 4
				U1..3				package: Smart1..3
								chip technology
					S			fast short tail IGBT chip
					E			low sat and fast IGBT chip
					T			fast trench IGBT
					P			soft switching trench IGBT
						1..n		internal reference
							B1..n	construction variation
							S1..n	electrical selection

Legend – Product name decipher

IGBT Modules

BSM	100	GB	120	DL	x	example for a IGBT module with an old designation
BSM						switch with IGBT and FWD
BYM						diode module
	100					max. DC-collector current (A)
		GA				single switch with one IGBT and FWD
		GB				half bridge (two IGBTs and FWDs)
		GD				3 phase full bridge (6-pack)
		GT				3 single switches with FWDs (tripack)
		GP				Power Intergrated Module
		GAL				chopper module (diode on collector side)
		GAR				chopper module (diode on emitter side)
		A				single diode
			120			collector-emitter-voltage in 10 V
				DL		Typ with low V_{CEsat}
				DN2		fast switching type
				DLC		low loss type with Emitter Controlled Diode
				S		with collector sense
				G		Design Variation
				Exxx		special type

Bridge Rectifiers and AC-Switches

TD	B6	H	K	135	N	16	L	OF	
DD									diode module
TT									thyristor module
TD									thyristor/diode
	B6								three phase bridge
	W3								three phase AC-switch
		C							fully controlled
		H							half controlled
		U							uncontrolled
			K						common cathode of thyristors
				135					output current (A) (W3C: RMS-current)
					N				phase control thyristor/diode
						16			repetitive peak off-state voltage in 100 V
							L		eupec™ IsoPACK™
							P		EconoBridge™ 4
							R		EconoBRIDGE™ without integr. brake chopper IGBT
							RR		EconoBRIDGE™ with integr. brake chopper IGBT
								O	no guaranteed turn-off time
								F	critical rate of rise of off-state voltage

Legend – Product name decipher

Presspacks

T	1190	N	18	T	O	F	VT	
T								thyristor
D								diode
	1190							maximum average on-state current (A)
	0							medium power ceramic disc
	1							high power ceramic disc
	3							light triggered thyristor disc
		N						phase control device
		K						phase control diode with cathode on case
		S						fast diode
		U						fast diode with cathode on case
		A						avalanche diode with anode on case
		B						avalanche diode with cathode on case
		SH						diode: soft recovery switch-off behavior
			18					maximum repetitive peak off-state and reverse voltage x 100 in V
				B				metric thread with cable
				C				metric thread with solder pin
				E				flat base
				T				disc
					O			no guaranteed turn-off time
								critical rate of off-state voltage
						C		500 V/µs
						F		1000 V/µs
						G		1500 V/µs
						H		2000 V/µs
							VT	on-state voltage class (thyristor)
								printed on housing
							VF	on-state voltage class (diode)
								printed on housing
					S01...n			electric selection
					B01...n			constructive variation

PowerBLOCK Modules

TT	162	N	16	K	O	F	-K	
TT								thyristor half bridge
DD								diode half bridge
ND								single diode
DZ								single diode
TZ								single thyristor
TD								thyristor/diode in half bridge housing
DT								diode/thyristor in half bridge housing
	162							maximum average on-state current (A)
		N						phase control device
		S						fast diode
			16					maximum repetitive off-state and reverse voltage x 100 in V
				K				module in pressure contact technology
				S				module in solder bond technology
				O				no guaranteed turn off time
								critical rate of of rise of off-state voltage (see disc devices)
						C		500 V/µs
						F		1000 V/µs
						G		1500 V/µs
						H		2000 V/µs
							-K	with common cathode terminal
							-A	with common anode terminal
					B01...n			constructive variation
					S01...n			electrical selection